

Product Summary

- $V_{DS} = -50V, I_D = -0.13A$
 $R_{DS(ON)} < 10 \Omega @ V_{GS} = -5V$

Application

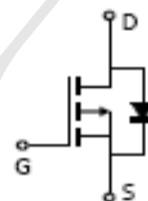
- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

Package and Pin Configuration

SOT-323



Circuit diagram



Marking:PD

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{DSS}	Drain-Source voltage	-50	V
V_{DGR}	Drain-Gate voltage	-50	V
V_{GSS}	Gate -Source voltage continuous	± 20	V
I_D	Drain current (Note1) continuous	-130	mA
P_D	Power Dissipation (Note1)	200	mW
$R_{\theta JA}$	Thermal resistance, Junction-to-Ambient	625	$^\circ C/W$
T_J, T_{stg}	Junction and Storage Temperature	-55 to +150	$^\circ C$

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-50	-75	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-1mA$	-0.8	-1.6	-2.0	
Gate-body Leakage Forward Reverse	I_{GSS}	$V_{DS}=0V, V_{GS}=20V$ $V_{DS}=0V, V_{GS}=-20V$	- -	- -	100 -100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-50V, V_{GS}=0V, T_J = 25^\circ\text{C}$	-	-	-15	μA
		$V_{DS}=-50V, V_{GS}=0V, T_J = 125^\circ\text{C}$			-60	
		$V_{DS}=-25V, V_{GS}=0V, T_J = 25^\circ\text{C}$	-	-	-100	
Forward transconductance	g_{FS}	$V_{DS}=-25V, I_D=100mA$	50	-	-	mS
Static drain-Source on-resistance	$R_{DS(ON)}$	$V_{GS}=-5.0V, I_D=100mA$	-	6	10	Ω
Input capacitance	C_{ISS}	$V_{DS}=-25V, V_{GS}=0V, f=1.0MHz$	-	-	45	pF
Output capacitance	C_{OSS}		-	-	25	
Reverse transfer capacitance	C_{RSS}		-	-	12	
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD} = -30V, I_D = -0.27A,$ $V_{GS} = -10V, R_{GEN} = 50\Omega$	-	10	-	ns
Turn-Off Delay Time	$t_{D(OFF)}$		-	18	-	ns



TECH PUBLIC

台丹电子

BSS84W

P-Channel Enhancement Mode Field Effect Transistor

www.sot23.com.tw

Characteristic Curves

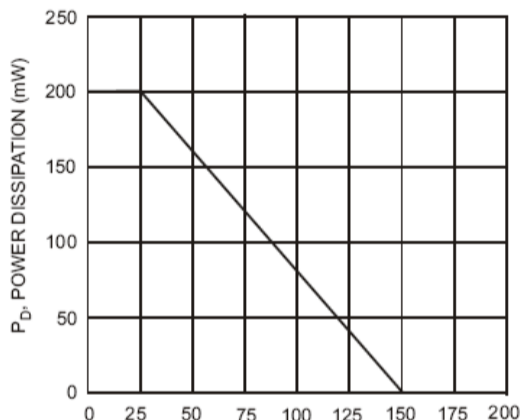


Fig. 1, Max Power Dissipation vs Ambient Temperature

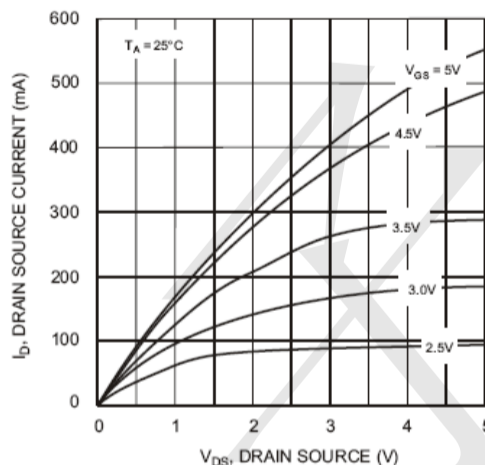


Fig. 2, Drain Source Current vs. Drain Source Voltage

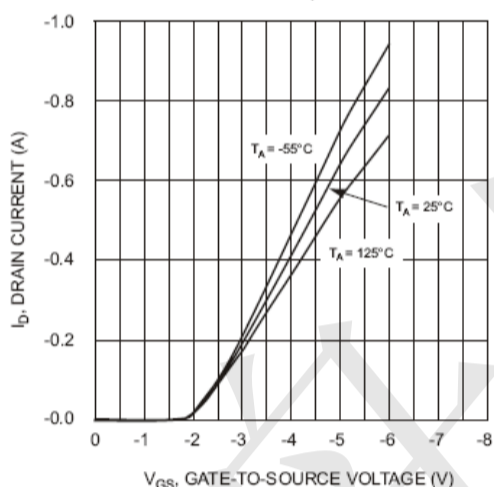


Fig. 3, Drain Current vs. Gate Source Voltage

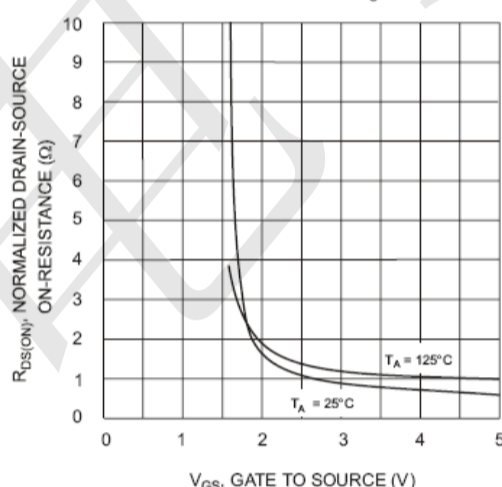


Fig. 4, On Resistance vs. Gate Source Voltage

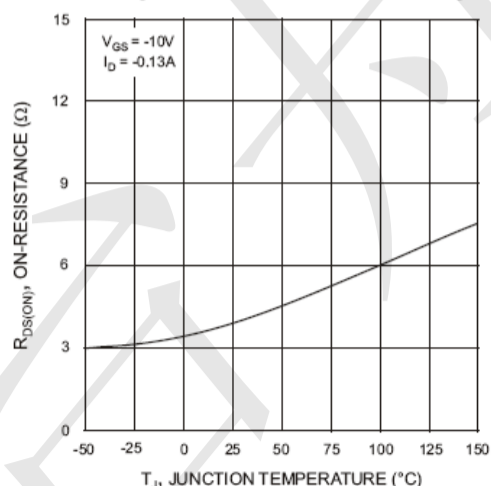


Fig. 5, On-Resistance vs. Junction Temperature

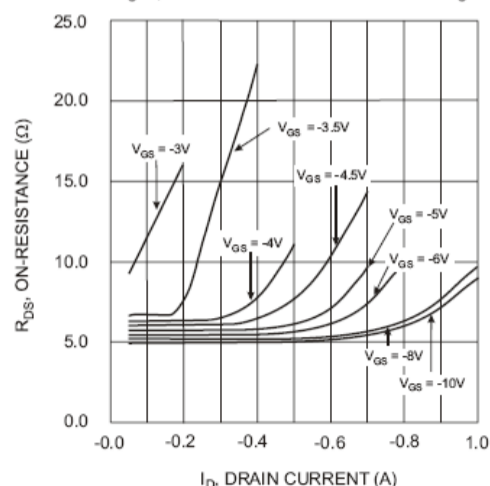
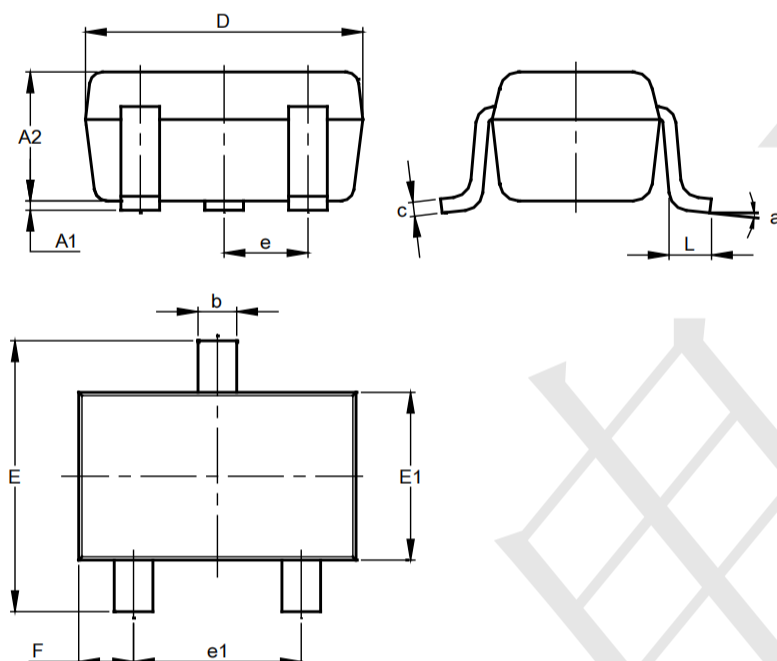


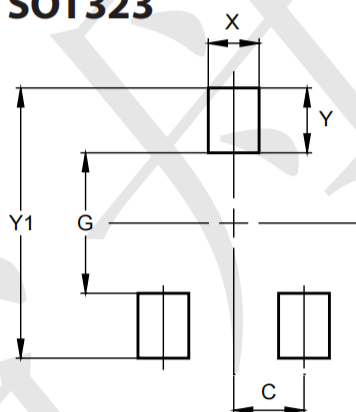
Fig. 6, On-Resistance vs. Drain Current

Outline Drawing - SOT323(SC70-3)



SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Land Pattern - SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500